

Optoelectronic component

5 The invention relates to an optoelectronic component having a photoactive layer disposed between an electrode and a counterelectrode.

Optoelectronic components, for instance solar cells or
10 LEDs, TFTs, etc., find wide use nowadays in everyday life and in the industrial sector.

For example, there are known thin-film solar cells which have a flexible configuration and hence allow
15 arrangement on curved surfaces. Solar cells of this kind preferably have active layers composed of amorphous silicon (a-Si) or CIGS (Cu(In,Ga)(S,Se)_2).

A particular disadvantage of these thin-film solar
20 cells is the high production costs, caused by the materials.

Also additionally known are solar cells having organic active layers with a flexible configuration (Konarka -
25 Power Plastic Series). The organic active layers may be formed from polymers (e.g. US7825326 B2) or small molecules (e.g. EP 2385556 A1). While it is a feature of polymers that they are not evaporable and therefore can only be applied from solutions, small molecules are
30 evaporable.

The advantage of such organic-based components over the conventional inorganic-based components (semiconductors such as silicon, gallium arsenide) is that some of the
35 optical absorption coefficients are extremely high (up to $2 \times 10^5 \text{ cm}^{-1}$), and so it is possible to produce very thin solar cells with a low material requirement and energy expenditure. Further technological aspects are the low costs, the possibility of producing flexible

large-area components on plastic films, and the virtually unlimited variation options and the unlimited availability of organic chemistry. A further advantage is the possibility of being able to produce transparent components which can be used in glass applications, for example.

A solar cell converts light energy to electrical energy. The term "photoactive" in the case of solar cells refers to the conversion of light energy to electrical energy. In contrast to inorganic solar cells, the light does not directly produce free charge carriers in organic solar cells; instead, excitons are formed at first, i.e. electrically neutral excited states (bound electron-hole pairs). Only in a second step are these excitons separated into free charge carriers which then contribute to the flow of electrical current.

A possible way of implementing an organic solar cell which has already been proposed in the literature is that of a pin diode having the following layer structure:

0. carrier, substrate,
1. base contact, usually transparent,
2. p layer(s),
3. i layer(s),
4. n layer(s),
5. top contact.

In this context, n and p respectively mean n- and p-doping leading to an increase in the density of free

electrons or holes in the thermal equilibrium state. However, it is also possible that the n layer(s) and p layer(s) are at least partly nominally undoped and only have preferentially n-conductive or preferentially p-conductive properties because of the material properties (for example different mobilities), because of unknown impurities (for example remaining residues from the synthesis, breakdown or reaction products during layer production), or because of environmental influences (for example adjoining layers, inward diffusion of metals or other organic materials, gas doping from the surrounding atmosphere). In this context, layers of this kind are considered primarily to be transport layers. The term "i layer", in contrast, refers to a nominally undoped layer (intrinsic layer). One or more i layers may consist here layers either of one material or a mixture of two or more materials (what are called interpenetrating networks or a bulk heterojunction). The incident light which enters through the transparent base contact produces excitons (bound electron-hole pairs) in the i layer or in the n/p layer. These excitons can be separated only by very high electrical fields or at suitable interfaces. In organic solar cells, sufficiently high fields are unavailable, and so all promising designs for organic solar cells are based on exciton separation at photoactive interfaces. The excitons diffuse to such an active interface, where electrons and holes are separated from one another. The material which accepts the electrons is referred to as acceptor, and the material which accepts the hole as donor. The separating interface may be between the p (n) layer and the i layer, or between two i layers. In the installed electrical field in the solar cell, electrons are then transported away to the n region and the holes to the p region. Preferably, the transport layers are transparent or substantially transparent materials having a large bandgap (wide-gap), as

described, for example, in WO 2004083958. Wide-gap materials refer here to materials having an absorption maximum in the wavelength range of < 450 nm, preferably < 400 nm.

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Means of adjusting the LUMO level or the HOMO level are known to those skilled in the art, in that very many organic materials having different positions of the energy levels of the HOMOs and LUMOs are known. The
10 adjustment is therefore effected by selecting and using a material having the desired position of the energy levels of the HOMO and LUMO. In addition, for example through the incorporation of electron-withdrawing or electron-donating groups, it is possible to lower or
15 increase the HOMO and LUMO levels of organic materials and hence to adjust a material according to the requirements.

Since the light always first produces excitons and does
20 not yet produce any free charge carriers, the low-recombination diffusion of excitons to the active interface plays a critical role in organic solar cells.

If the i layer is a mixed layer, the function of light
25 absorption is assumed either by just one of the components or else by both. The advantage of mixed layers is that the excitons produced have to cover just a very short distance before they arrive at a domain boundary where they are separated. The electrons and
30 holes are transported away separately into the respective materials. Since the materials are in contact throughout the mixed layer, it is crucial in the case of this concept that the separate charges have a long lifetime on the particular material, and
35 continuous percolation paths exist for both charge carrier types from any point to the respective contact.

To date, in the field of small molecules, the absorber layer thicknesses have been limited to about 30-40 nm (in the best case 60 nm), whereas up to 200 nm are possible in the polymer field while maintaining a good fill factor (FF) (> 60%). The reason is the poorer transport of charge carriers in SM-OPVs (organic solar cells comprising small molecules), since there is no on-chain transport, in contrast to polymers. In the field of organic solar cells comprising small molecules, the problem has been solved to date by ever higher extinction coefficients (in solution, up to 100 000 or higher), which have led to good efficiencies combined with good FF. Because of the cyanine limit, however, this is not capable of infinite improvement. Therefore, there is a search for solutions by which mixed donor-acceptor layers (called bulk heterojunctions, BHJs) can be made thicker, in order to increase the quantum yield.

It is an object of the present invention to specify an optoelectronic component and a process for producing an optoelectronic component having an improved quantum yield.

The object is achieved by an optoelectronic component as claimed in claim 1. Advantageous configurations are specified in the dependent claims.

It would be possible to achieve an increased quantum yield through an increase in the layer thickness of the photoactive layer. However, problems here are the occurrence of torsion in the oligomer units and excessive crystallization, which often causes short circuits.

According to the invention, therefore, an optoelectronic component comprising at least one photoactive layer is proposed, wherein the photoactive

layer comprises a mixed multiple layer containing at least three materials, wherein at least one organic material is composed of small molecules, wherein at least one material is a donor and at least one material is an acceptor, wherein the donor and the acceptor form a donor-acceptor system with at least one third material which is set up so as to affect the propensity of the donor and/or acceptor to crystallize.

10 In the context of the present invention, small molecules are understood to mean non-polymeric organic molecules having monodisperse molar masses between 100 and 2000, which are in the solid phase under standard pressure (air pressure of the surrounding atmosphere) and at room temperature. More particularly, these small molecules may also be photoactive, "photoactive" being understood to mean that the molecules undergo a change in charge state when energy is supplied. Energy supply is understood to mean light energy supply, for example visible light or UV light, or else electrical energy supply.

In one embodiment of the invention, the third material has an energy level at which the magnitude of the LUMO $\leq$ the LUMO of the acceptor, and the magnitude of the HOMO $\geq$ the HOMO of the donor. The difference between HOMO and LUMO of the third material is therefore greater than or at least equal to the difference between the HOMO of the donor and the LUMO of the acceptor, as per fig. 30.

The terms "HOMO" and "LUMO" are understood, as usual in chemistry, to mean highest occupied molecular orbital and lowest unoccupied molecular orbital. The term relates both to individual molecules and to solids or material films. The energy levels of HOMO and LUMO can be determined in the manner known to those skilled in

the art, for example via cyclic voltammetry (CV) or ultraviolet photoelectron spectroscopy (UPS).

5 In a further embodiment of the invention, the third material has an energy level where the magnitude of the LUMO of the third material is preferably 0.3 eV lower than the LUMO of the acceptor material of the photoactive layer and/or the magnitude of the HOMO of the third material is 0.3 eV above the magnitude of the
10 energy level of the HOMO of the donor material of the photoactive layer.

In a further embodiment of the invention, the proportion of the third material in the photoactive
15 layer is < 10%.

In a further embodiment of the invention, the proportion of the third material in the photoactive layer is between 10% and 50%.

20 In a further embodiment of the invention, the proportion of the third material in the photoactive layer is 0.1% by weight < x < 30% by weight, preferably 0.1% by weight < x < 20% by weight, more preferably
25 0.1% by weight < x < 10% by weight.

In a further embodiment of the invention, the third material simultaneously improves charge transport within the photoactive layer.

30 In a further embodiment of the invention, at least one donor material in the photoactive layer is an oligomer.

In the context of the invention, oligomers are
35 understood to mean non-polymeric organic molecules which have monodisperse molar masses between 100 and 2000 and are in the solid phase under standard pressure

(air pressure of the surrounding atmosphere) and at room temperature.

5 In a further embodiment of the invention, at least one donor material D1 in the photoactive layer is an oligomer, where the magnitude of the HOMO of the donor material D1 is equal to the magnitude of the HOMO of the third material and the magnitude of the LUMO of the donor material D1 is equal to the magnitude of the LUMO
10 of the third material.

In a further embodiment of the invention, the third material is an oligomer.

15 In a further embodiment of the invention, the third material is set up so as to prevent crystallization of donor and/or acceptor. At the same time, the third material may be a hole conductor, an electron conductor or an ambipolar transporting material, where the latter
20 may also, for example, be a mixture of electron and hole conductor.

In a further embodiment of the invention, the third material, because of its molecular structure, minimizes
25 crystallization of the donor and/or acceptor phase. By virtue of the better mixing of donor and acceptor, it is possible for more excitons to reach a separating interface and to be separated into charge carriers and hence to contribute to the current.

30 In a further embodiment of the invention, the molecular structure of the third material is substantially similar to the molecular structure of the donor material D1, as a result of which the third material
35 acts as a lattice defect in the donor material D1, and so the donor material D1 does not crystallize too significantly as a pure phase.

A lattice defect (also lattice imperfection or crystal defect) refers to any irregularity in an otherwise periodic crystal lattice. The existence of lattice imperfections distinguishes a real crystal from the theoretical model of an ideal crystal. Lattice imperfections are of fundamental significance for many properties of a crystal, especially for the chemical reactivity, mass transfer and diffusion within the crystal, and for the mechanical properties thereof. The lattice defects are classified with reference to the spatial extent of the defect area. The number of spatial dimensions in which the lattice defect has more than an atomic extent is identified. In this way, zero- to three-dimensional lattice defects are distinguished.

In one embodiment of the invention, the molecular structure of the third material is set up such that the third material causes a lattice defect in the donor and/or acceptor material.

In one embodiment of the invention, the molecular structure of the third material is substantially similar to the structure of the acceptor material A1, as a result of which the third material acts as a lattice defect in the acceptor material A1, and so the acceptor material A1 does not crystallize too significantly as a pure phase.

In a further embodiment of the invention, the third material is set up such that the crystallization of donor material and/or acceptor material is improved. In this case, the third material ensures phase separation and hence improves charge transport in the individual phases by creating more continuous conduction pathways. The improved phase separation can be demonstrated, for example, by a reduced photoluminescence signal in the triple mixed layer compared to that without the third material.

In a further embodiment of the invention, the third material is selected such that the third material establishes a minimum separation between the acceptor and donor, wherein the third material simultaneously contributes to the phase separation of the acceptor and donor. Thus, the problem of "geminal recombination" can be reduced.

10 In the context of the invention, geminal recombination is understood to mean the recombination of already separated charge carriers with one another.

In a further embodiment of the invention, the third material, in its molecular structure, has a first region set up to be fullerenophilic and a second region set up to be fullerophobic, wherein the first and second regions are set up with spatial separation.

20 In the context of the invention, fullerenophilic is understood to mean a molecular structure or at least part of a molecular structure which has a preference for proximity to fullerenes (C_{60} , C_{70} , etc.).

25 In the context of the invention, fullerophobic is understood to mean a molecular structure or at least part of a molecular structure which has a preference for remoteness from fullerenes (C_{60} , C_{70} , etc.).

30 In a further embodiment of the invention, the optoelectronic component has more than one photoactive layer between the electrode and the counterelectrode. The component may take the form, for instance, of a tandem cell or triple cell. This is especially advantageous since the incident light passes through several photoactive layers within the component. Particularly advantageously, the various absorber layers are matched to one another, the absorber layers

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having different absorption maxima. This enables efficient utilization of the incident light.

5 In a further embodiment of the invention, at least one of the photoactive layers, as acceptor, comprises a material from the group of the fullerenes or fullerene derivatives.

10 In a further embodiment of the invention, at least one doped, partly doped or undoped transport layer is disposed between the electrode and the counterelectrode.

15 In a further embodiment of the invention, the optoelectronic component is semitransparent at least within a certain light wavelength range.

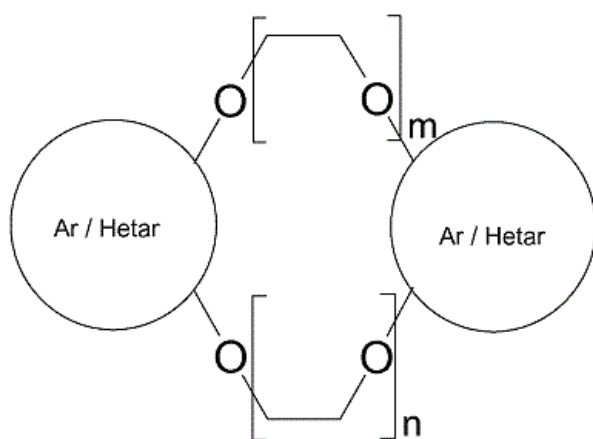
20 In a further embodiment of the invention, the optoelectronic component is an organic solar cell.

In a further embodiment of the invention, the component is a pin single, pin tandem cell, pin multiple cell, nip single cell, nip tandem cell or nip multiple cell.

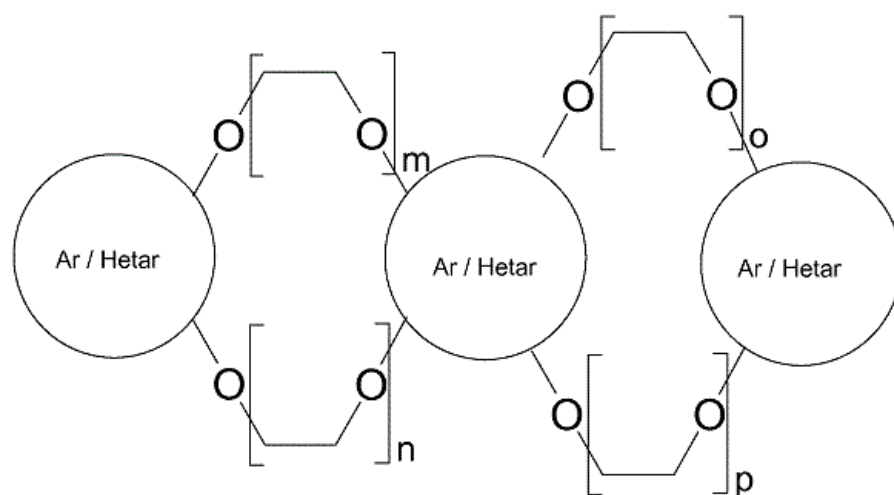
25 In a further embodiment of the invention, the component consists of a combination of nip, ni, ip, pnip, pni, pip, nipn, nin, ipn, pnipn, pnin or pipn structures in which a plurality of independent combinations containing at least one i layer are stacked.

30 In a further embodiment of the invention, the third material is selected from a group consisting of crown ethers, triphenyls, sorbitols, quinacridones, bis(4-(tert-butyl)benzoato-O)hydroxyaluminum.

35 In a further embodiment of the invention, as the third material, crown ethers of the general formula (Ia and Ib) are selected.



(Ia)



(Ib)

5 with Ar = phenyl, biphenyl, triphenyl, naphthyl, binaphthyl, 3-6 fused phenyl rings (e.g. anthracenyl, phenanthrenyl, pyrenyl)

Hetar = thiophene, pyrrole, furan, oxazole, thiazole,
 10 oxadiazole, thiadiazole, triazole, pyridine, pyrimidine, pyrazine, benzothiophenes, benzopyrrole, benzofuran, benzothiofene, benzopyrrole, benzofuran, benzoxazole, benzothiazole, thienothiophenes, thienopyrrole, thienofuran, 3-6 fused heterocycles,
 15 dithienothiophene, dithienopyrrole, dithienobenzene, dithienocyclopentadienes, dipyrrolobenzene,

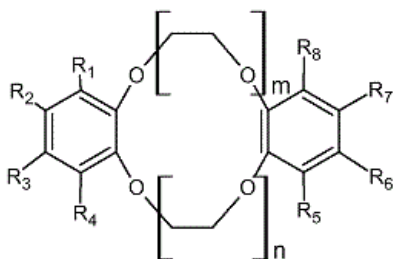
ether bridges joined in 1,2, 1,3 and 1,4 positions on the particular phenyl ring (ortho, meta and para positions), naphthyl ring, fused phenyl ring, and heteroaryl ring and fused heteroaryl ring,

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m and n are each independently 1, 2, 3, 4, 5, 6,

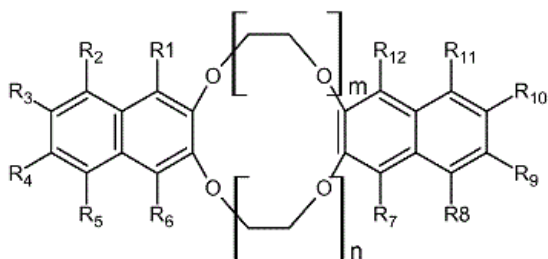
o and p are each independently 0, 1, 2, 3, 4, 5, 6.

10 More particularly, dibenzo-crown ethers and dinaphtho-crown ethers and mixed benzo-/naphtho-crown ethers are used. Preference is given to compounds having the following structures:

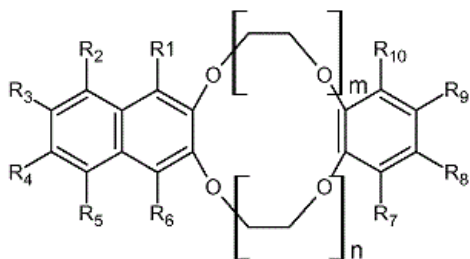


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or

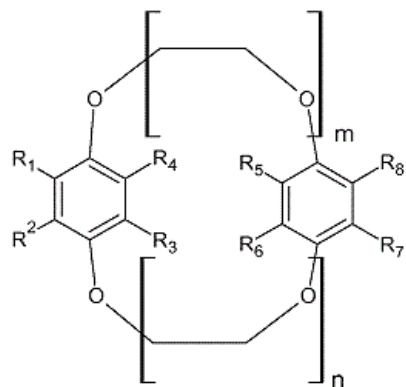
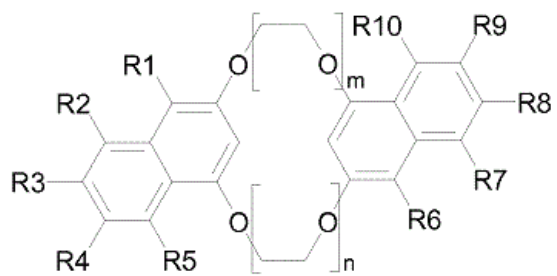


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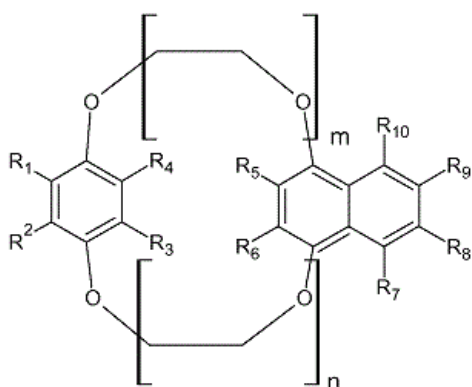


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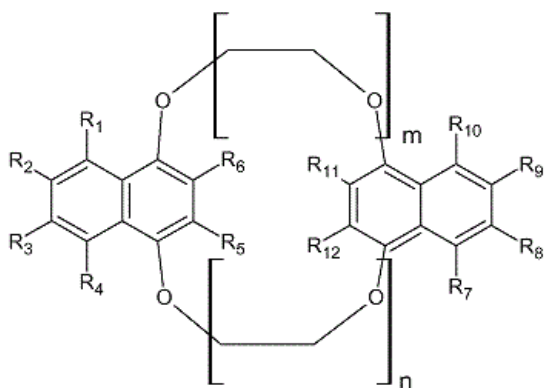


or



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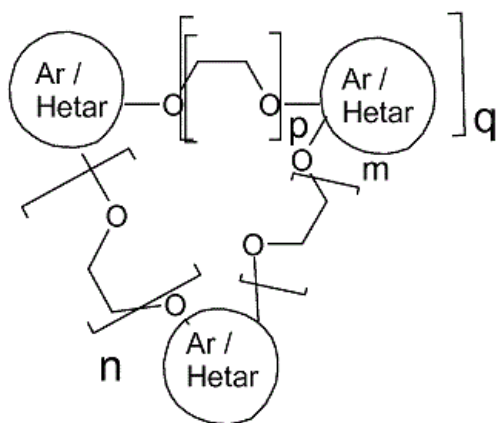
or



where in each case: n and m are each independently
10 selected from 3, 4 and 5, and

R₁, R₂, R₃, R₄, R₅, R₆, R₇, R₈, R₉, R₁₀, R₁₁ and R₁₂ are each independently selected from H, CH₃, C₂H₅, C₃H₇, C₄H₉, C₅H₁₁, C₆H₁₃, isobutyl, CF₃, C₂F₅, C₃F₇, C₄F₉, C₅F₁₁, C₆F₁₃, OH, O-CH₃, CH₂-O-CH₃, CH₂-O-CH₂-CH₃, CN, phenyl, thiophene.

In one embodiment of the invention, the crown ethers have the following general formula (II):



(II)

with Ar = phenyl, naphthyl, biphenyl, triphenyl, naphthyl, binaphthyl, 3-6 fused phenyl rings, anthracenyl, phenanthrenyl, pyrenyl,

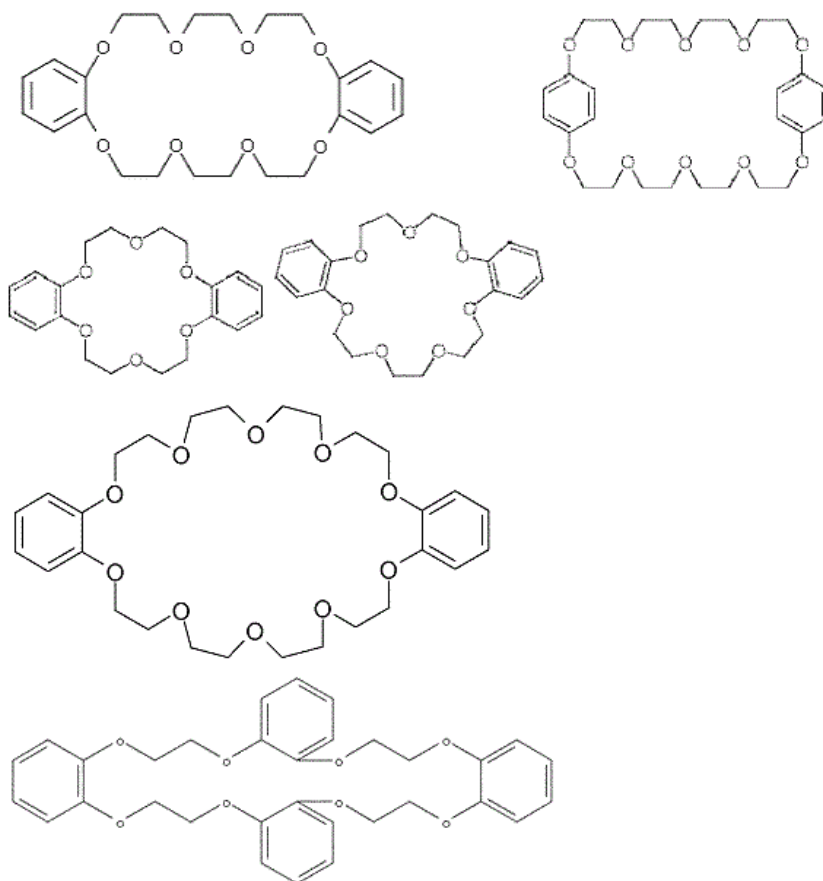
Hetar = thiophene, pyrrole, furan, thienothiophenes, oxazole, thiazole, oxadiazole, thiadiazole, triazole, pyridine, pyrimidine, pyrazine, benzothiophenes, benzopyrrole, benzofuran, benzothiophene, benzopyrrole, benzofuran, benzoxazole, benzothiazole, thienothiophenes, thienopyrrole, thienofuran, 3-6 fused heterocycles, dithienothiophene, dithienopyrrole, dithienobenzene, dithienocyclopentadienes, dipyrrolobenzene,

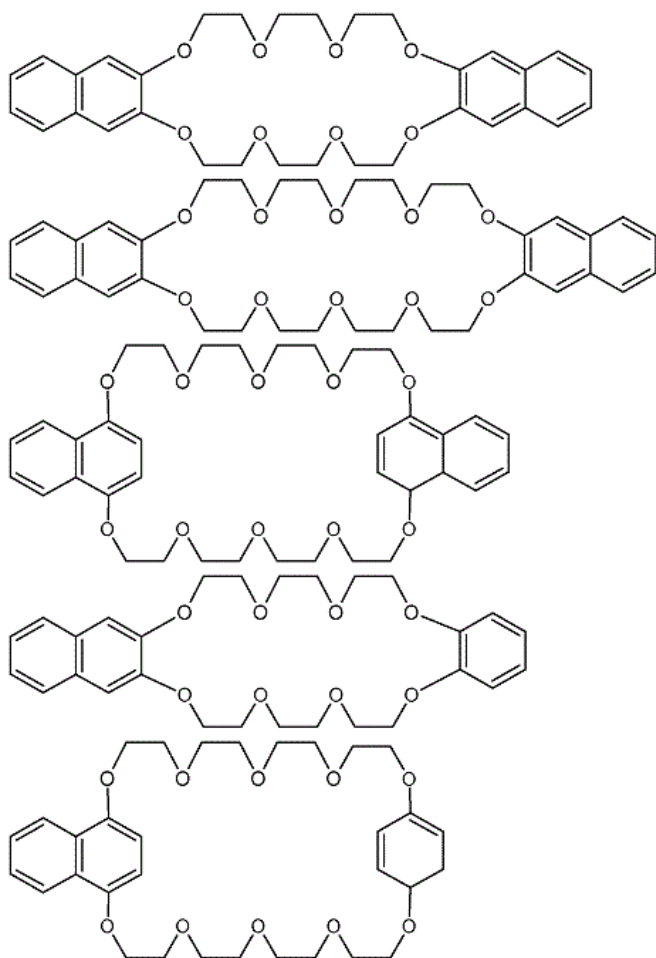
ether bridges joined in 1,2, 1,3 and 1,4 positions on the particular phenyl ring (ortho, meta and para positions), naphthyl ring, fused phenyl ring, and heteroaryl ring and fused heteroaryl ring,

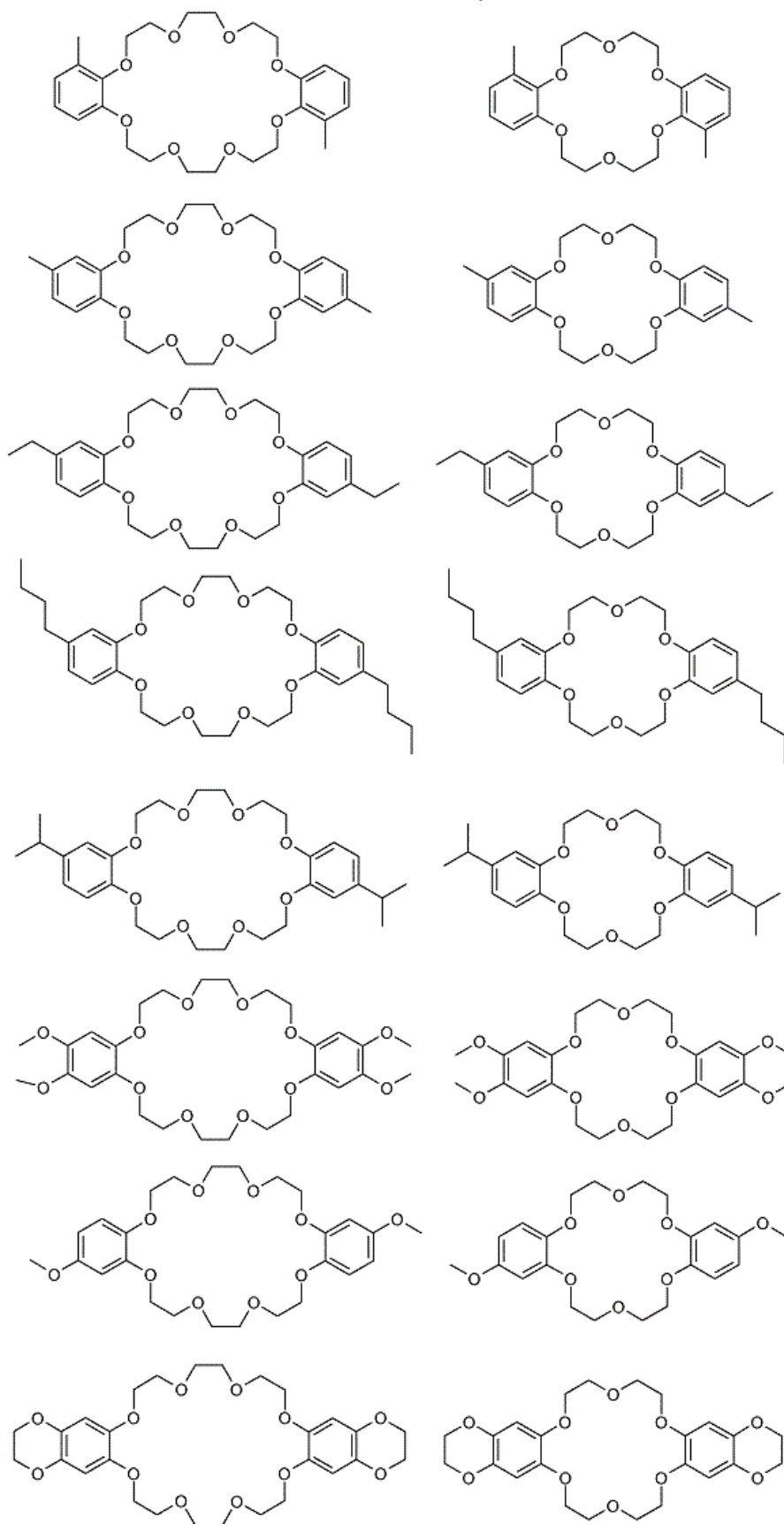
m and n are each independently 1, 2, 3, 4, 5, 6,

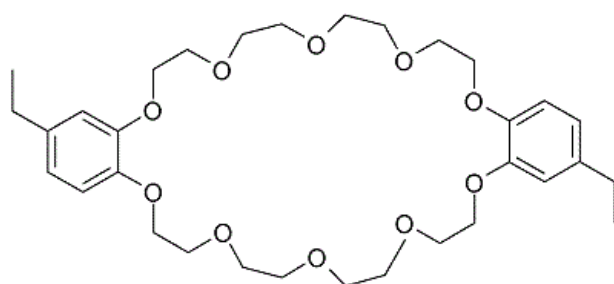
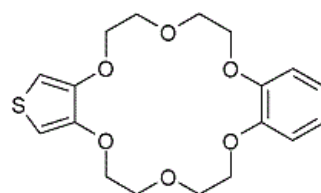
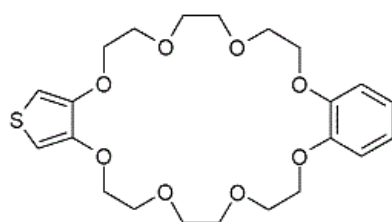
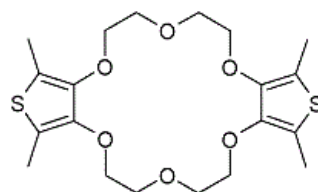
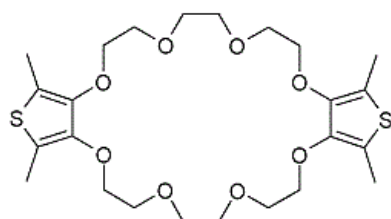
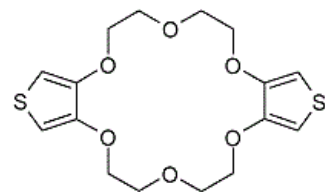
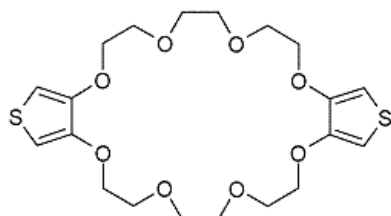
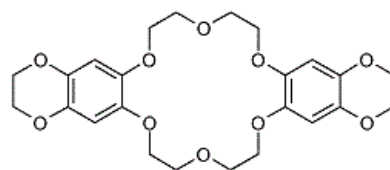
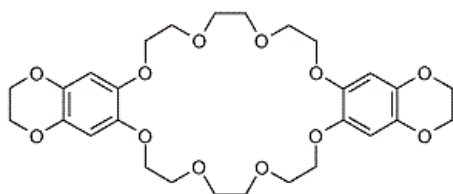
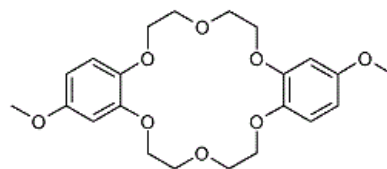
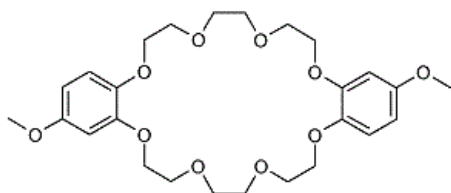
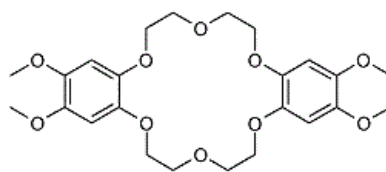
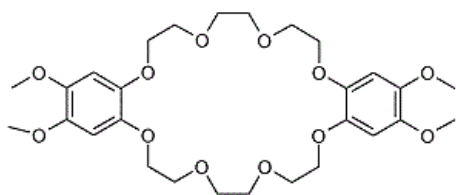
p and q are each independently 1, 2, 3, 4, 5, 6.

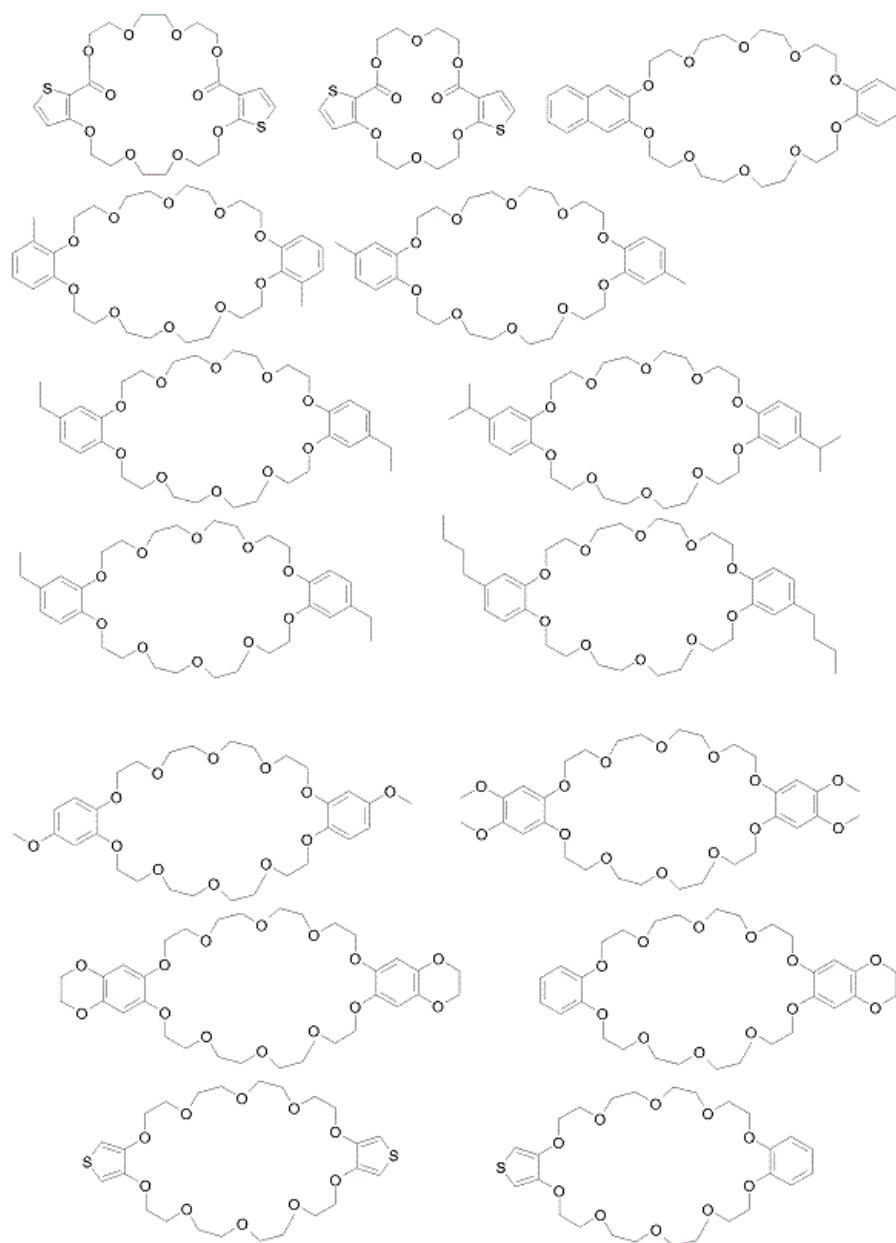
Particular preference is given to compounds having the
5 following structures:

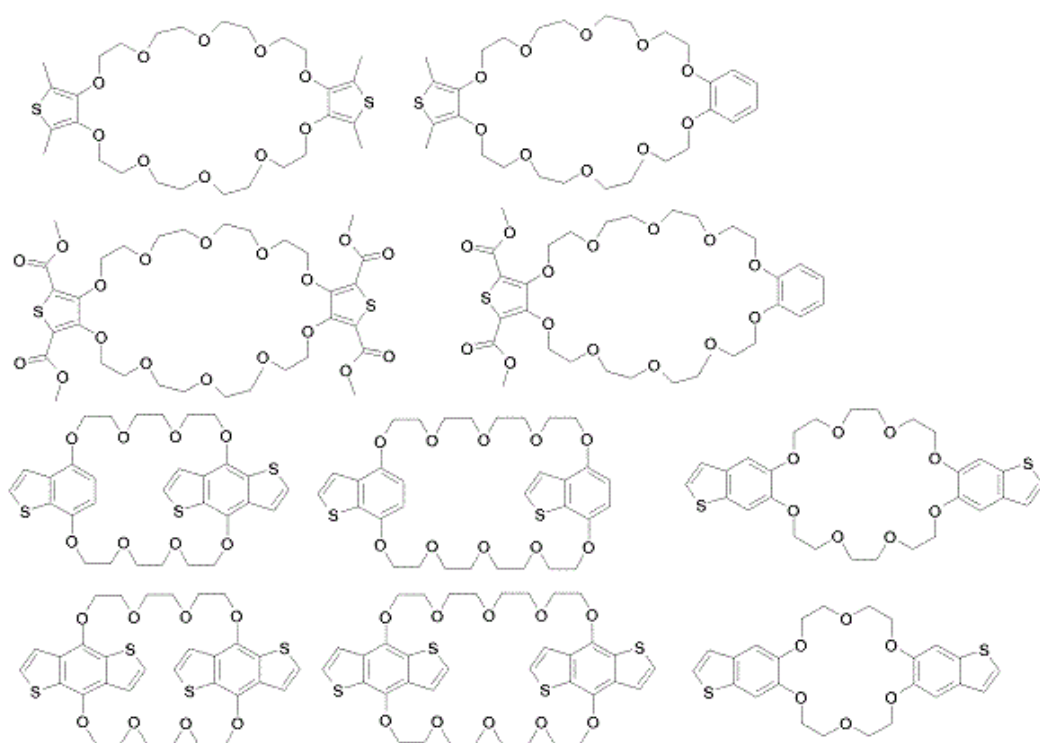


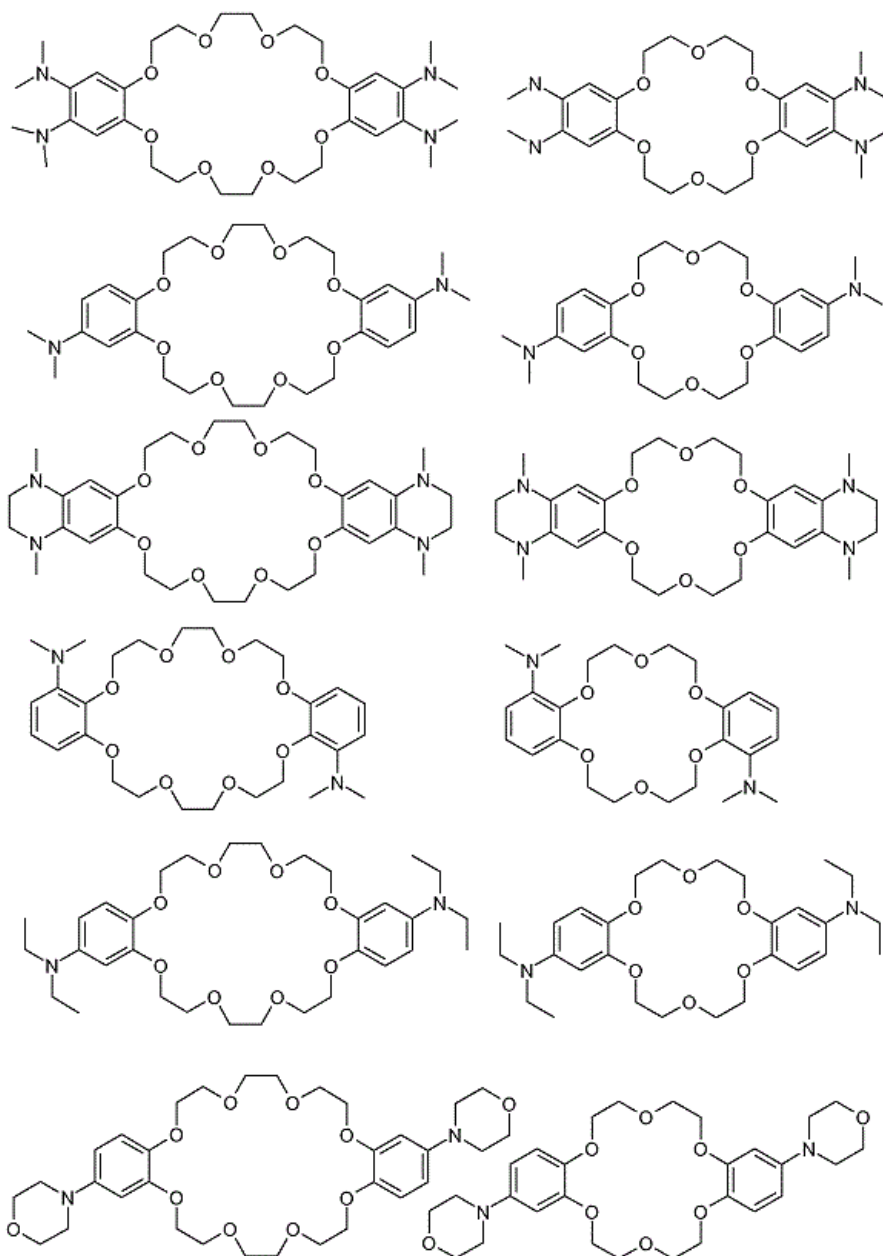








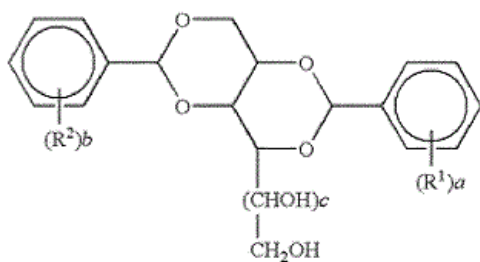




In one embodiment of the invention, the crown ethers
 5 are selected from a group consisting of aryl and
 heteroaryl crown ethers and fused aryl and fused
 heteroaryl crown ethers, preferably diaryl and
 diheteroaryl crown ethers and mixed aryl and heteroaryl
 crown ethers, more preferably dibenzo-crown ethers,
 10 dinaphtho-crown ethers and mixed benzo-naphtho-crown
 ethers. An aryl crown ether consists of at least one
 aryl group, but may also have a bi-, tri- and
 polycyclic aromatic hydrocarbyl group. Two carbon atoms

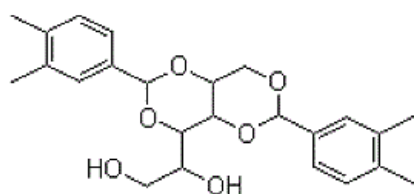
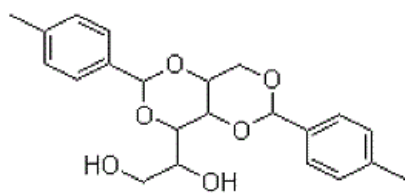
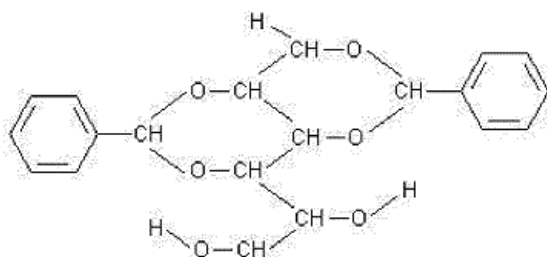
of the aryl base skeleton therein are joined to form a ring with monoethoxy, diethoxy, triethoxy, tetraethoxy, pentaethoxy and hexaethoxy groups. A fused aryl crown ether consists of at least one bicyclic aromatic hydrocarbyl group, but may also have a tri- and polycyclic aromatic hydrocarbyl group. Two carbon atoms of the fused base skeleton therein are joined to form a ring with monoethoxy, diethoxy, triethoxy, tetraethoxy, pentaethoxy and hexaethoxy groups. A fused heteroaryl crown ether consists of at least one heteroaryl ring with at least one benzene ring or a further heteroaryl ring fused thereto, but may also have a tri- and polycyclic heteroaromatic hydrocarbyl group. Two carbon atoms of the fused base skeleton therein are joined to form a ring with monoethoxy, diethoxy, triethoxy, tetraethoxy, pentaethoxy and hexaethoxy groups. A diaryl crown ether consists of two non-fused (separate) aryl groups joined to one another via alkoxy bridges in the form of a crown. These alkoxy units consist of one to six ethoxy groups. A fused diaryl crown ether consists of two fused aryl groups joined to one another via two alkoxy bridges in the form of a crown. These alkoxy units consist of one to six ethoxy groups. A fused diheteroaryl crown ether consists of two fused heteroaryl groups joined to one another via two alkoxy bridges in the form of a crown. These alkoxy units consist of one to six ethoxy groups. An aryl-heteroaryl crown ether consists both of an aryl group and of a heteroaryl group joined to one another via two alkoxy bridges in the form of a crown. These alkoxy units consist of one to six ethoxy groups.

In a further embodiment of the invention, the third material is a sorbitol. Preference is given to compounds having the following structures:

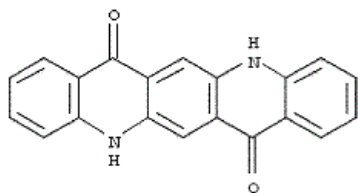


where R1 and R2 are each independently selected from H, CH₃, C₂H₅ and

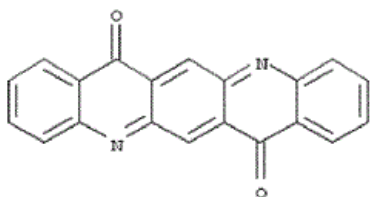
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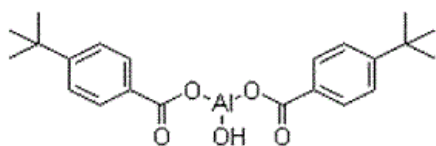
In a further embodiment of the invention, the third
10 material is a quinacridone. Preference is given to
compounds having the following structures:



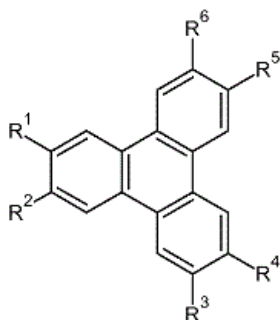
or



In a further embodiment of the invention, the third material is bis(4-tert-butylbenzoato-O)hydroxyaluminum
5 having the following structure:



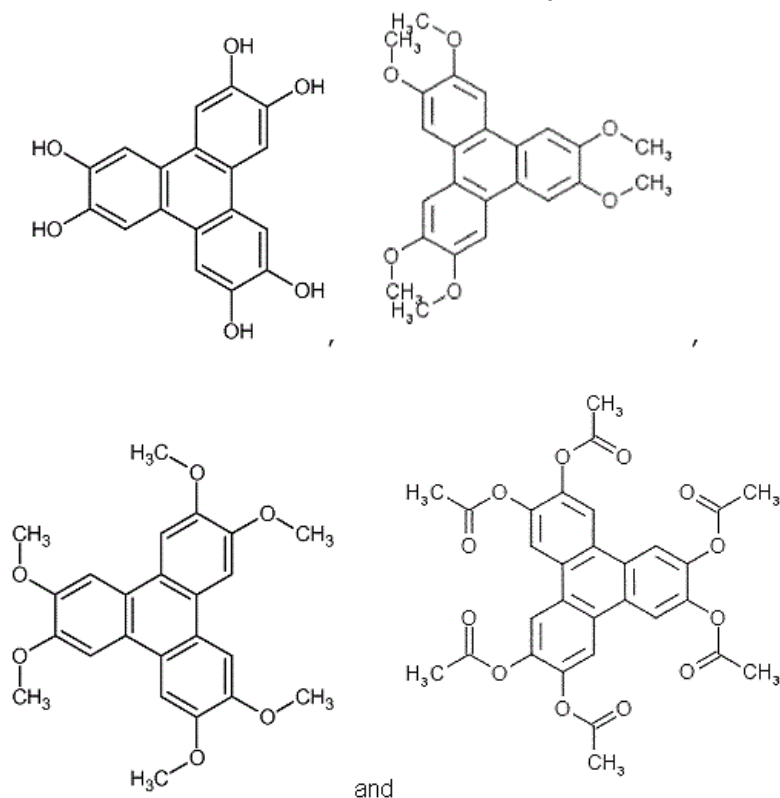
In a further embodiment of the invention, the third
10 material is a triphenyl having the following structure:



where R1 to R6 are each independently selected from H,
15 OH, OCH₃, OOCCH₃, where at least three oxygens are present in the molecule.

Preference is given to compounds having the following structures:

20



Preferred developments of the invention are apparent
 5 from the combinations of the claims or individual
 features thereof.

The invention is to be illustrated in detail
 hereinafter with reference to some working examples and
 10 figures. The working examples are intended to describe
 the invention without restricting it. The figures show:

Fig. 1 a schematic diagram of an inventive component,

15 Fig. 2 a current-voltage characteristic of a
 comparative component having two materials in the
 photoactive layer,

Fig. 3 a current-voltage characteristic of a component
 20 having the same layer structure as shown in Fig. 2, but
 with three materials in the photoactive layer, using
 compound (I) as the third material,

Fig. 4 a current-voltage characteristic of a comparative component having two materials in the photoactive layer,

5 Fig. 5 a current-voltage characteristic of a component having the same layer structure as shown in Fig. 4, but with three materials in the photoactive layer, using compound (I) as the third material,

10 Fig. 6 a current-voltage characteristic of a comparative component having two materials in the photoactive layer,

Fig. 7 a current-voltage characteristic of a component
15 having the same layer structure as shown in Fig. 6, but with three materials in the photoactive layer, using compound (I) as the third material,

Fig. 8 a current-voltage characteristic of a
20 comparative component having two materials in the photoactive layer,

Fig. 9 a current-voltage characteristic of a component
25 having the same layer structure as shown in Fig. 8, but with three materials in the photoactive layer, using compound (II) as the third material,

Fig. 10 a current-voltage characteristic of a
30 comparative component having two materials in the photoactive layer,

Fig. 11 a current-voltage characteristic of a component
having the same layer structure as shown in Fig. 10,
but with three materials in the photoactive layer,
35 using compound (V) as the third material,

Fig. 12 a current-voltage characteristic of a comparative component having two materials in the photoactive layer,

5 Fig. 13 a current-voltage characteristic of a component having the same layer structure as shown in Fig. 12, but with three materials in the photoactive layer, using compound (VI) as the third material,

10 Fig. 14 a current-voltage characteristic of a comparative component having two materials in the photoactive layer, deposited at substrate temperature 70°C,

15 Fig. 15 a current-voltage characteristic of a component having the same layer structure as shown in Fig. 14, but with three materials in the photoactive layer, using compound (III) as the third material and with deposition at room temperature,

20

Fig. 16 a current-voltage characteristic of a comparative component having two materials in the photoactive layer, deposited at substrate temperature 70°C, and

25

Fig. 17 a current-voltage characteristic of a component having the same layer structure as shown in Fig. 16, but with three materials in the photoactive layer, using compound (I) as the third material and with deposition at room temperature,

30

Fig. 18 a current-voltage characteristic of a comparative component having two materials in the photoactive layer, deposited at substrate temperature 70°C,

35

Fig. 19 a current-voltage characteristic of a component having the same layer structure as shown in Fig. 18,

but with three materials in the photoactive layer,
using compound (VI) as the third material and with
deposition at room temperature,

5 Fig. 20 a current-voltage characteristic of a
comparative component having two materials in the
photoactive layer,

Fig. 21 a representation of the external quantum
10 efficiency of a comparative component having two
materials in the photoactive layer,

Fig. 22 a representation of the fill factor
characteristics and the open-circuit voltage of a
15 comparative component having two materials in the
photoactive layer as a function of insolation,

Fig. 23 a current-voltage characteristic of a component
of the invention having three materials in the
20 photoactive layer,

Fig. 24 a representation of the external quantum
efficiency of a component having three materials in the
photoactive layer,

25 Fig. 25 a representation of the fill factor
characteristics and the open-circuit voltage of a
component of the invention having three materials in
the photoactive layer as a function of insolation,

30 Fig. 26 a current-voltage characteristic of a
comparative component having two materials in the
photoactive layer,

35 Fig. 27 a representation of the external quantum
efficiency of a comparative component having two
materials in the photoactive layer,

Fig. 28 a current-voltage characteristic of a component of the invention having three materials in the photoactive layer,

5 Fig. 29 a representation of the external quantum efficiency of a component having three materials in the photoactive layer and

Fig. 30 a schematic diagram of an energy scheme with
10 three materials.

In a working example of the invention, fig. 1 shows a schematic of a component 1 executed, by way of example, as inorganic solar cell. Component 1 is disposed on a
15 transparent substrate 2 which is preferably executed in a flexible manner, for instance as a film. Disposed atop the substrate 2 is an electrode 3 which is executed from metal, a conductive oxide, especially ITO, ZnO:Al or other TCOs or a conductive polymer, for
20 instance PEDOT:PSS or PANI. Disposed atop the electrode 3 is a charge carrier transport layer 4 executed, for example, as an electron or hole transport layer. Disposed atop this charge carrier transport layer 4 is a photoactive layer 5 comprising at least one donor
25 material and one acceptor material which together form a donor-acceptor system. In addition, the photoactive layer comprises a third material having a proportion of 0.1% by weight $< x < 10\%$ by weight. This third material is selected from a group consisting of crown ethers, triphenyls, sorbitols, quinacridones, bis(4-(tert-
30 butyl)benzoato-O)hydroxyaluminum. Disposed atop the photoactive layer 5 is a further charge carrier transport layer 6. This charge carrier transport layer 6 likewise takes the form of an electron or hole transport layer, the charge carrier transport layer 6
35 being set up to be complementary to the charge carrier transport layer 4. Disposed atop this charge carrier

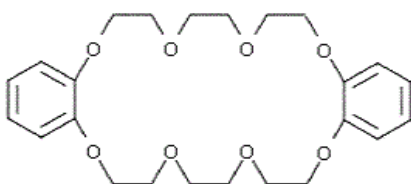
transport layer 6 is a counterelectrode 7 formed, for example, from a metal, for instance Al.

In a second working example, the component 1 of the invention has a photoactive layer 5 comprising three materials, wherein a donor material D1 and an acceptor material A1 form a donor-acceptor system. The donor material D1 is, for example, a material from the class of the phthalocyanines, perylene derivatives, TPD derivatives, oligothiophenes or a material as disclosed in WO2006092134 A1, WO2011161262 or WO2011161170A1. The acceptor material A1 is, for example, a fullerene or fullerene derivative (C60, C70, etc.). The photoactive layer 5 further comprises a third material which takes the form of a further donor material D2. The third material D2 affects the propensity of the donor material D1 to crystallize. In an alternative configuration, the third material is an acceptor material A2 which affects the propensity of the acceptor material A1 to crystallize.

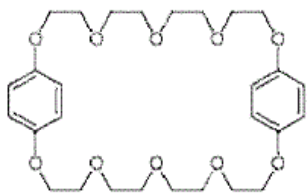
In a further working example, the photoactive component 1 has, for example, the following structure:

ITO / C60 / photoactive mixed layer / BPAPF (9,9-bis[4-[N,N-bis(biphenyl-4-yl)amino]phenyl]-9H-fluorene) / BPAPF:NDP9 / NDP9 / Au

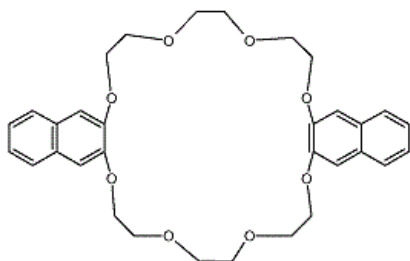
wherein the photoactive mixed layer comprises, as third material, one of the following compounds in an addition of < 7%:



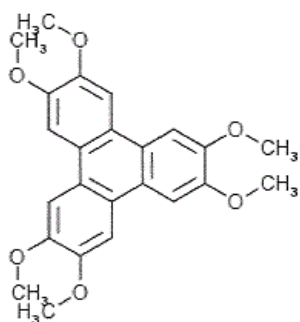
Compound (I)



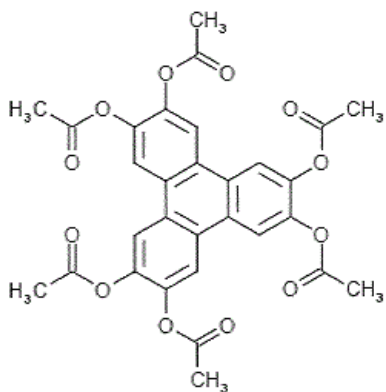
Compound (II)



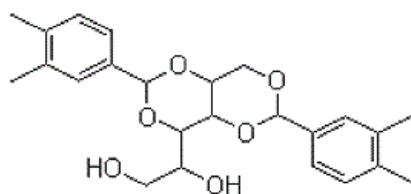
Compound (III)



Compound (IV)



Compound (V)



Compound (VI)

In a further working example, figs. 2 and 3 show the test results for a component 1 having a photoactive layer 5 with a donor-acceptor system in the form of a graph, where the photoactive layer 5 has a layer thickness of 30 nm. The photoactive layer 5 was deposited at a substrate temperature of 70°C. Fig. 2 shows the current-voltage characteristic of a component

1 with a donor-acceptor system, and fig. 3 a current-voltage characteristic for a component with a photoactive layer comprising the donor-acceptor system and compound (I). The photoactive layer 5 in the components differs here only in terms of the addition of the compound (I). In this case, a rise in the fill factor (FF) from 46% to 58.6% caused by the addition of compound (I) is found.

10 It can be inferred from the comparison of the fill factors (FF) that the addition of the third material has a significant influence on the current generated.

In a further working example, figs. 4 and 5 show the test results for a component 1 having a photoactive layer 5 with a different donor-acceptor system in the form of a graph, where the photoactive layer 5 has a layer thickness of 30 nm. The photoactive layer 5 was deposited at a substrate temperature of 70°C. Fig. 4 shows the current-voltage characteristic of a component 1 with a donor-acceptor system, and fig. 5 a current-voltage characteristic for a component with a photoactive layer comprising the donor-acceptor system and compound (I). The photoactive layer 5 in the components differs here only in terms of the addition of the compound (I). In this case, a rise in the fill factor (FF) from 48.8% to 65.7% caused by the addition of compound (I) is found.

30 In a further working example, figs. 6 and 7 show the test results for a component 1 having a photoactive layer 5 with a third donor-acceptor system in the form of a graph, where the photoactive layer 5 has a layer thickness of 30 nm. The photoactive layer 5 was deposited at a substrate temperature of 70°C. Fig. 6 shows the current-voltage characteristic of a component 1 with a donor-acceptor system, and fig. 7 a current-voltage characteristic for a component with a

photoactive layer comprising the donor-acceptor system and compound (I). The photoactive layer 5 in the components differs here only in terms of the addition of the compound (I). In this case, a rise in the fill factor (FF) from 50.7% to 62.7% caused by the addition of compound (I) is found.

In a further working example, figs. 8 and 9 show the test results for a component 1 having a photoactive layer 5 with a donor-acceptor system in the form of a graph, where the photoactive layer 5 has a layer thickness of 30 nm. The photoactive layer 5 was deposited at a substrate temperature of 70°C. Fig. 8 shows the current-voltage characteristic of a component 1 with a donor-acceptor system, and fig. 9 a current-voltage characteristic for a component with a photoactive layer comprising the donor-acceptor system and compound (II). The photoactive layer 5 in the components differs here only in terms of the addition of the compound (II). In this case, a rise in the fill factor (FF) from 46% to 50.6% caused by the addition of compound (II) is found.

In a further working example, figs. 10 and 11 show the test results for a component 1 having a photoactive layer 5 with a further donor-acceptor system in the form of a graph, where the photoactive layer 5 has a layer thickness of 30 nm. The photoactive layer 5 was deposited at a substrate temperature of 70°C. Fig. 10 shows the current-voltage characteristic of a component 1 with a donor-acceptor system, and fig. 11 a current-voltage characteristic for a component with a photoactive layer comprising the donor-acceptor system and compound (V). The photoactive layer 5 in the components differs here only in terms of the addition of the compound (V). In this case, a rise in the fill factor (FF) from 48.8% to 60.2% caused by the addition of compound (V) is found.

In a further working example, figs. 12 and 13 show the test results for a further component 1 having a photoactive layer 5 with a donor-acceptor system in the form of a graph, where the photoactive layer 5 has a layer thickness of 30 nm. The photoactive layer 5 was deposited at a substrate temperature of 70°C. Fig. 12 shows the current-voltage characteristic of a component 1 with a donor-acceptor system, and fig. 13 a current-voltage characteristic for a component with a photoactive layer comprising the donor-acceptor system and compound (VI). The photoactive layer 5 in the components differs here only in terms of the addition of the compound (VI). In this case, a rise in the fill factor (FF) from 48.8% to 60.3% caused by the addition of compound (VI) is found.

In a further working example, figs. 14 and 15 show the test results for a further component 1 having a photoactive layer 5 with a donor-acceptor system in the form of a graph, where the photoactive layer 5 has a layer thickness of 30 nm. The photoactive layer 5 was deposited at a substrate temperature of 70°C. Fig. 14 shows the current-voltage characteristic of a component 1 with a donor-acceptor system, and fig. 15 a current-voltage characteristic for a component with a photoactive layer comprising the donor-acceptor system and compound (III). The photoactive layer 5 in the components differs here only in terms of the addition of the compound (III). In this case, a rise in the fill factor (FF) from 60.0% to 65.2% caused by the addition of compound (III) is found.

In a further working example, figs. 16 and 17 show the test results for a component 1 having a photoactive layer 5 with a donor-acceptor system in the form of a graph, where the photoactive layer 5 has a layer thickness of 30 nm. The photoactive layer 5 was

deposited at a substrate temperature of 70°C in the case of fig. 16 and at room temperature in the case of fig. 17. Fig. 16 shows the current-voltage characteristic of a component 1 with a donor-acceptor system, and fig. 17 a current-voltage characteristic for a component with a photoactive layer comprising the donor-acceptor system and compound (I). The photoactive layer 5 in the components differs here in terms of the addition of the compound (I) and the substrate temperature in the deposition of the photoactive layer 5. In this case, it is found that the fill factors are virtually the same at 64% (fig. 16) and 63.6% (fig. 17). Through the addition of compound (I), it is thus possible to achieve the same fill factor at lower substrate temperatures as in the case of heated substrates without addition. Through the addition, it is thus possible to achieve more simplified conditions in the deposition.

In a further working example, figs. 18 and 19 show the test results for a component 1 having a photoactive layer 5 with a donor-acceptor system in the form of a graph, where the photoactive layer 5 has a layer thickness of 30 nm. The photoactive layer 5 was deposited at room temperature in the case of fig. 18 and in the case of fig. 19. Fig. 18 shows the current-voltage characteristic of a component 1 with a donor-acceptor system, and fig. 19 a current-voltage characteristic for a component with a photoactive layer comprising the donor-acceptor system and compound (VI). The photoactive layer 5 in the components differs here in terms of the addition of the compound (VI) and the substrate temperature in the deposition of the photoactive layer 5. In this case, it is found that the fill factors, at 55.1% (fig. 18) and 60.9% (fig. 19) are increased by addition of the compound (VI).

In a further working example, the component 1 of the invention has a photoactive layer 5 comprising three materials, wherein a donor material D1 and an acceptor material A1 form a donor-acceptor system. The donor material D1 is, for example, a material from the class of the phthalocyanines, perylene derivatives, TPD derivatives, oligothiophenes or a material as disclosed in WO2006092134 A1, WO2011161262 or WO2011161170A1. The acceptor material A1 is, for example, a fullerene or fullerene derivative (C60, C70, etc.). The photoactive layer 5 further comprises a third material which takes the form of a further donor material D2. The third material D2 affects the propensity of the donor material D1 to crystallize. In an alternative configuration, the third material is an acceptor material A2 which affects the propensity of the acceptor material A1 to crystallize.

In a further working example, figs. 20 to 22 show the test results for a component 1 having a photoactive layer 5 with a donor-acceptor system in the form of a graph, where the photoactive layer 5 has a layer thickness of 20 nm (11) or of 30 nm (12). Fig. 20 shows the current-voltage characteristics of component 1, fig. 21 the representation of the external quantum efficiency and fig. 22 a plot of the fill factor (FF) and the open-circuit voltage (U_{oc}) against irradiance.

In a further working example, figs. 23 to 25 show the test results for a component 1 having a photoactive layer 5 with a donor-acceptor system having further donor D2 as third material in the form of a graph, where the photoactive layer 5 has a layer thickness of 20 nm (13) or of 30 nm (14) and has been added in each case in a ratio of 1:1:1. Fig. 23 shows the current-voltage characteristics of inventive component 1, fig. 24 the representation of the external quantum

efficiency and fig. 25 a plot of the fill factor (FF) and the open-circuit voltage (U_{oc}) against irradiance.

It can be inferred from the comparison of the characteristic values of fill factor (FF) and current generated that the addition of the third material has a significant influence on the current generated. Particularly the comparison of fig. 21 and fig. 24 shows the influence of the third material on the external quantum efficiency, which is much more marked in fig. 24 compared to fig. 21.

In a further working example, figs. 26 and 27 show the test results for a component 1 having a photoactive layer 5 with a donor-acceptor system in the form of a graph, where the photoactive layer 5 has a layer thickness of 20 nm (15) or of 30 nm (16). Fig. 26 shows the current-voltage characteristics of component 1 and fig. 27 the representation of the external quantum efficiency.

In a further working example, figs. 28 and 29 show the test results for a component 1 having a photoactive layer 5 with a donor-acceptor system having further donor D2 as third material in the form of a graph, where the photoactive layer 5 has a layer thickness of 20 nm (17) or of 30 nm (18). The layer 5 has a ratio of acceptor:donorD1:donorD2 = 1:1:0.1. Fig. 28 shows the current-voltage characteristics of inventive component 1 and fig. 29 the representation of the external quantum efficiency.

It can be inferred from the comparison of the characteristic value of fill factor (FF) that the addition of the third material donor D2 has a significant influence on the fill factor. Particularly the comparison of fig. 26 and fig. 28 shows the

influence of the third material on the fill factor, which is higher in fig. 28 compared to fig. 26.

5 In a further working example, fig. 30 shows an energy
scheme of a component having a photoactive layer with a
donor material, an acceptor material and a third
material. The HOMO position of the donor material 10
and the LUMO position of the donor material 11 can be
inferred from fig. 30. In addition, fig. 30 shows the
10 HOMO position of the acceptor 20 and the LUMO position
of the acceptor 21. In addition, fig. 30 shows the HOMO
position of the third material 30 and the LUMO position
of the third material 31. As can be inferred from fig.
30, this has a HOMO position 30 of an order of
15 magnitude equal to or greater than the HOMO position of
the donor material, and a LUMO position 31 of an order
of magnitude equal to or less than the LUMO position of
the acceptor, i.e. between the LUMO position of the
acceptor and the vacuum level. The vacuum level of the
20 energy is represented by reference numeral 40.

Optoelectronic component

5

List of reference numerals

	1 optoelectronic component
	2 substrate
10	3 electrode
	4 charge carrier transport layer (ETL or HTL)
	5 photoactive layer
	6 charge carrier transport layer (ETL or HTL)
	7 counterelectrode
15	10 HOMO position of the donor material
	11 LUMO position of the donor material
	20 HOMO position of the acceptor material
	21 LUMO position of the acceptor material
	30 HOMO position of the third material
20	31 LUMO position of the third material
	40 vacuum level of energy

Optoelectronic component

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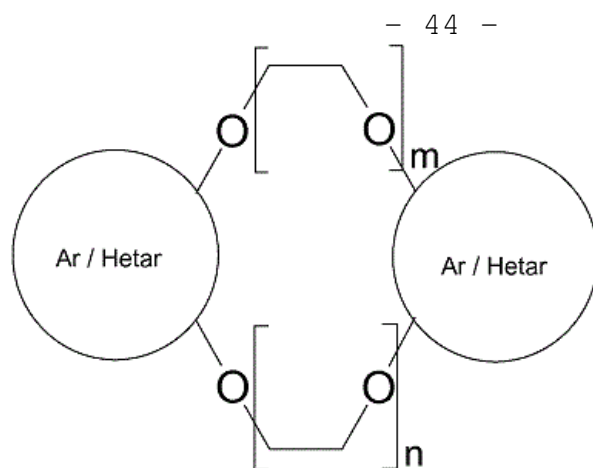
Claims

1. An optoelectronic component (1) comprising at least one photoactive layer (5) disposed between an
10 electrode (3) and a counterelectrode (7), wherein the photoactive layer (5) comprises a mixed multiple layer containing at least three materials, wherein at least one material is an organic material composed of small molecules, wherein at
15 least one material is a donor and at least one material is an acceptor, wherein the donor and the acceptor form a donor-acceptor system and at least one third material which is set up so as to affect the propensity of the donor and/or acceptor to
20 crystallize.
2. The optoelectronic component as claimed in claim 1,
characterized in that the third material has an energy level at which the magnitude of the LUMO $\leq$
25 the magnitude of the LUMO of the acceptor, and the magnitude of the HOMO $\geq$ HOMO of the donor.
3. The optoelectronic component as claimed in either of claims 1 and 2, **characterized in that** the third
30 material has an energy level where the magnitude of the LUMO of the third material is 0.3 eV lower than the magnitude of the LUMO of the acceptor material of the photoactive layer (5) and/or the magnitude of the HOMO of the third material is 0.3 eV greater
35 than the magnitude of the energy level of the HOMO of the donor material of the photoactive layer (5).

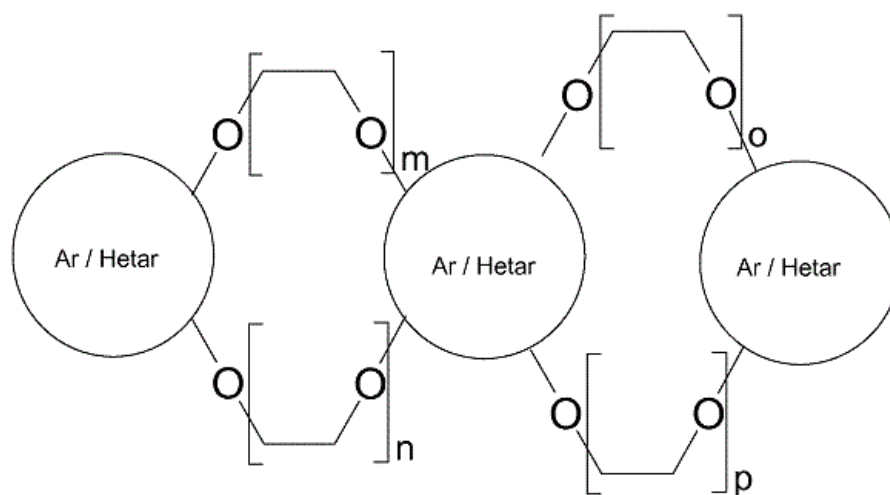
4. The optoelectronic component as claimed in any of the preceding claims, **characterized in that** the proportion of the third material in the photoactive layer (5) is 0.1% by weight < x < 30% by weight, preferably 0.1% by weight < x < 20% by weight, more preferably 0.1% by weight < x < 10% by weight.
5. The optoelectronic component as claimed in any of the preceding claims, **characterized in that** at least one donor material in the photoactive layer (5) is an oligomer.
6. The optoelectronic component as claimed in any of the preceding claims, **characterized in that** the third material is an oligomer.
7. The optoelectronic component as claimed in any of the preceding claims, **characterized in that** the third material is set up such that the third material, because of its molecular structure, minimizes crystallization of the donor and/or acceptor phase.
8. The optoelectronic component as claimed in any of the preceding claims, **characterized in that** crystallization of donor and/or acceptor is prevented.
9. The optoelectronic component as claimed in any of the preceding claims, **characterized in that** the molecular structure of the third material is set up such that the third material causes a lattice defect in the donor and/or acceptor material.
10. The optoelectronic component as claimed in any of the preceding claims, **characterized in that** the third material is selected such that the third material establishes a minimum separation between

the acceptor and donor, wherein the third material simultaneously contributes to the phase separation of the acceptor and donor.

- 5 11. The optoelectronic component as claimed in any of
the preceding claims, **characterized in that** the
third material is set up such that the third
material, because of its molecular structure,
promotes crystallization of the donor and/or
10 acceptor phase.
12. The optoelectronic component as claimed in any of
the preceding claims, **characterized in that** the
third material, in its molecular structure, has a
15 first region set up to be fullerenophilic and a
second region set up to be fullerenophobic, wherein
the first and second regions are set up with
spatial separation.
- 20 13. The optoelectronic component as claimed in any of
the preceding claims, **characterized in that** the
third material is selected from a group consisting
of crown ethers, triphenyls, sorbitols,
quinacridones, bis(4-(tert-butyl)benzoato-O)-
25 hydroxyaluminum.
14. The optoelectronic component as claimed in claim
13, **characterized in that** the crown ethers are
selected from a group of the general formula (Ia)
30 or (Ib)



(Ia)



(Ib)

with Ar = phenyl, biphenyl, triphenyl, naphthyl,
 5 binaphthyl, 3-6 fused phenyl rings, anthracenyl,
 phenanthrenyl, pyrenyl

Hetar = thiophene, pyrrole, furan, oxazole,
 thiazole, oxadiazole, thiadiazole, triazole,
 10 pyridine, pyrimidine, pyrazine, benzothiophenes,
 benzopyrrole, benzofuran, benzothiophene, benzo-
 pyrrole, benzofuran, benzoxazole, benzothiazole,
 thienothiophenes, thienopyrrole, thienofuran, 3-6
 fused heterocycles, dithienothiophene, dithieno-
 15 pyrrole, dithienobenzene, dithienocyclopentadienes,
 dipyrrolobenzene,

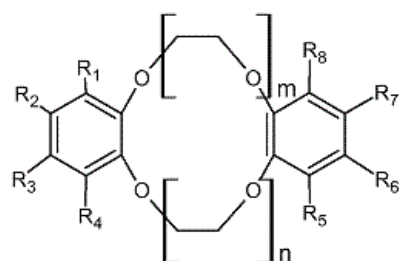
ether bridges joined in 1,2, 1,3 and 1,4 positions on the particular phenyl ring (ortho, meta and para positions), naphthyl ring, fused phenyl ring, and heteroaryl ring and fused heteroaryl ring,

5

m and n are each independently 1, 2, 3, 4, 5, 6,

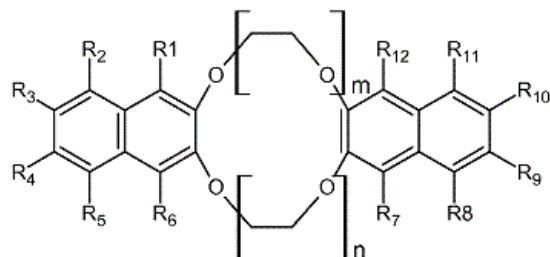
o and p are each independently 0, 1, 2, 3, 4, 5, 6.

- 10 15. The optoelectronic component as claimed in claim 14, **characterized in that** the crown ethers are compounds of the following structures:

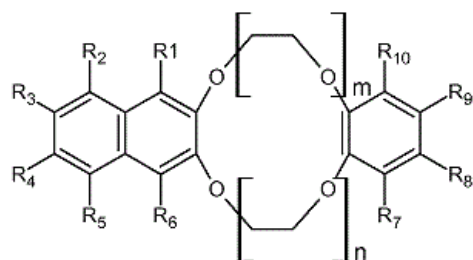


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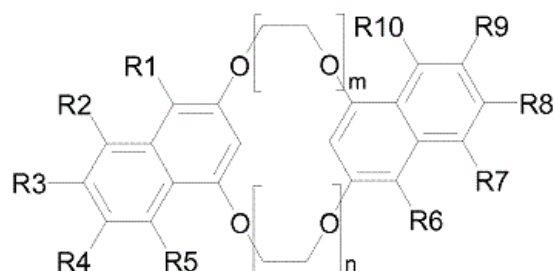
or



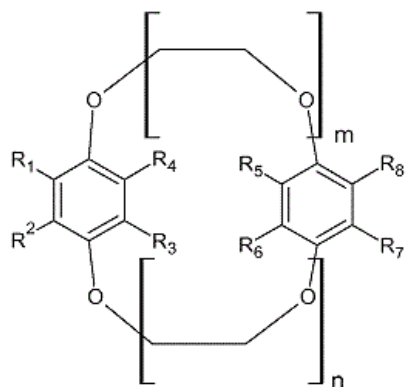
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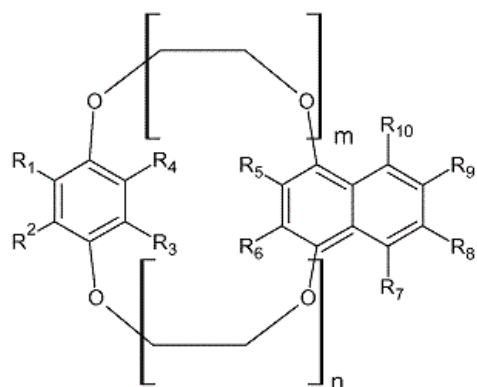
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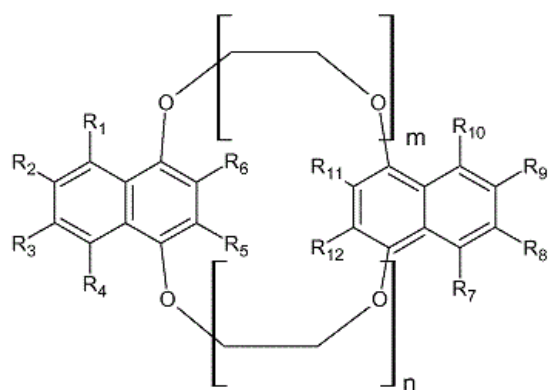
20



or



or



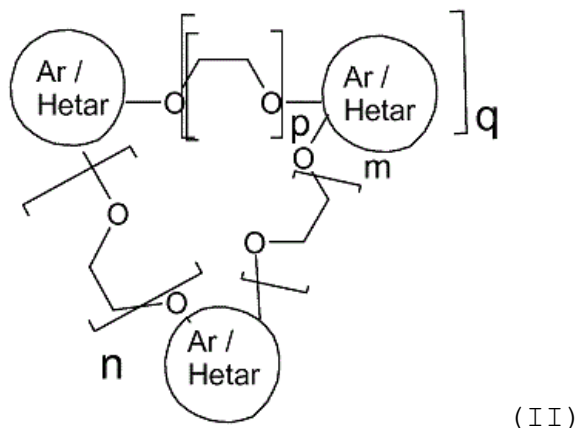
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where in each case: n and m are each independently selected from 3, 4 and 5, and

10 $R_1, R_2, R_3, R_4, R_5, R_6, R_7, R_8, R_9, R_{10}, R_{11}$ and R_{12} are each independently selected from H, CH₃, C₂H₅, C₃H₇, C₄H₉, C₅H₁₁, C₆H₁₃, isobutyl, CF₃, C₂F₅, C₃F₇, C₄F₉, C₅F₁₁, C₆F₁₃, OH, O-CH₃, CH₂-O-CH₃, CH₂-O-CH₂-CH₃, CN, phenyl, thiophene.

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16. The optoelectronic component as claimed in claim 13, **characterized in that** the crown ethers have the following general formula (II):



with Ar = phenyl, biphenyl, triphenyl, naphthyl, binaphthyl, 3-6 fused phenyl rings (anthracenyl, phenanthrenyl, pyrenyl, ...),

Hetar = thiophene, pyrrole, furan, oxazole, thiazole, oxadiazole, thiadiazole, triazole, pyridine, pyrimidine, pyrazine, benzothiophenes, benzopyrrole, benzofuran, benzothiophene, benzopyrrole, benzofuran, benzoxazole, benzothiazole, thienothiophenes, thienopyrrole, thienofuran, 3-6 fused heterocycles, dithienothiophene, dithienopyrrole, dithienobenzene, dithienocyclopentadienes, dipyrrolobenzene,

ether bridges joined in 1,2, 1,3 and 1,4 positions on the particular phenyl ring (ortho, meta and para positions), naphthyl ring, fused phenyl ring, and heteroaryl ring and fused heteroaryl ring,

m and n are each independently 1, 2, 3, 4, 5, 6,

p and q are each independently 1, 2, 3, 4, 5, 6.

17. The optoelectronic component as claimed in any of the preceding claims, **characterized in that** the optoelectronic component (1) is an organic solar cell.

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18. The use of crown ethers as claimed in any of claims 14 to 16 in photoactive layers of optoelectronic components.